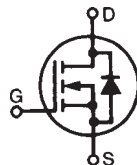


## HiPerFET™ Power MOSFETs

## IXFK24N100 IXFX24N100

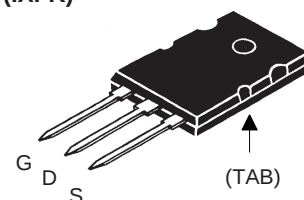
N-Channel Enhancement Mode  
Avalanche Rated  
Fast Intrinsic Diode



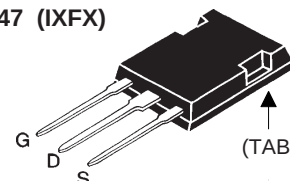
$$\begin{aligned} V_{DSS} &= 1000V \\ I_{D25} &= 24A \\ R_{DS(on)} &\leq 390m\Omega \\ t_{rr} &\leq 250ns \end{aligned}$$

| Symbol        | Test Conditions                                                    | Maximum Ratings            |                    |
|---------------|--------------------------------------------------------------------|----------------------------|--------------------|
| $V_{DSS}$     | $T_J = 25^\circ C$ to $150^\circ C$                                | 1000                       | V                  |
| $V_{DGR}$     | $T_J = 25^\circ C$ to $150^\circ C$ , $R_{GS} = 1M\Omega$          | 1000                       | V                  |
| $V_{GSS}$     | Continuous                                                         | $\pm 20$                   | V                  |
| $V_{GSM}$     | Transient                                                          | $\pm 30$                   | V                  |
| $I_{D25}$     | $T_C = 25^\circ C$                                                 | 24                         | A                  |
| $I_{DM}$      | $T_C = 25^\circ C$ , pulse width limited by $T_{JM}$               | 96                         | A                  |
| $I_A$         | $T_C = 25^\circ C$                                                 | 24                         | A                  |
| $E_{AS}$      | $T_C = 25^\circ C$                                                 | 3                          | J                  |
| $dV/dt$       | $I_S \leq I_{DM}$ , $V_{DD} \leq V_{DSS}$ , $T_J \leq 150^\circ C$ | 5                          | V/ns               |
| $P_D$         | $T_C = 25^\circ C$                                                 | 560                        | W                  |
| $T_J$         |                                                                    | -55 ... +150               | $^\circ C$         |
| $T_{JM}$      |                                                                    | 150                        | $^\circ C$         |
| $T_{stg}$     |                                                                    | -55 ... +150               | $^\circ C$         |
| $T_L$         | 1.6mm (0.062 in.) from case for 10s                                | 300                        | $^\circ C$         |
| $T_{SOLD}$    | Plastic body for 10s                                               | 260                        | $^\circ C$         |
| $M_d$         | Mounting force (PLUS247)<br>Mounting torque (TO-264)               | 20..120/4.5..27<br>1.13/10 | N/lb.<br>Nm/lb.in. |
| <b>Weight</b> | PLUS247                                                            | 6                          | g                  |
|               | TO-264                                                             | 10                         | g                  |

TO-264 (IXFK)



PLUS247 (IXFX)



G = Gate      D = Drain  
S = Source      TAB = Drain

### Features

- International standard packages
- Low  $R_{DS(on)}$  HDMOS™ process
- Rugged polysilicon gate cell structure
- Avalanche rated
- Low package inductance
- Fast intrinsic rectifier

### Applications

- DC-DC converters
- Battery chargers
- Switched-mode and resonant-mode power supplies
- DC choppers
- AC motor drives
- Temperature and lighting controls

### Advantages

- PLUS 247™ package for clip or spring mounting
- Space savings
- High power density

| Symbol       | Test Conditions<br>( $T_J = 25^\circ C$ , unless otherwise specified) | Characteristic Values |      |                     |
|--------------|-----------------------------------------------------------------------|-----------------------|------|---------------------|
|              |                                                                       | Min.                  | Typ. | Max.                |
| $BV_{DSS}$   | $V_{GS} = 0V$ , $I_D = 3mA$                                           | 1000                  |      | V                   |
| $V_{GS(th)}$ | $V_{DS} = V_{GS}$ , $I_D = 8mA$                                       | 3.0                   |      | 5.5 V               |
| $I_{GSS}$    | $V_{GS} = \pm 20V$ , $V_{DS} = 0V$                                    |                       |      | $\pm 200$ nA        |
| $I_{DSS}$    | $V_{DS} = V_{DSS}$<br>$V_{GS} = 0V$<br>$T_J = 125^\circ C$            |                       |      | 100 $\mu A$<br>2 mA |
| $R_{DS(on)}$ | $V_{GS} = 10V$ , $I_D = 0.5 \cdot I_{D25}$ , Note 1                   |                       |      | 390 m $\Omega$      |

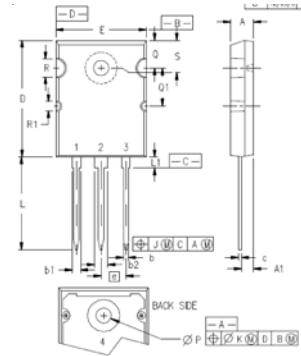
| Symbol       | Test Conditions<br>( $T_J = 25^\circ\text{C}$ , unless otherwise specified)                                                                        | Characteristic Values |      |                         |
|--------------|----------------------------------------------------------------------------------------------------------------------------------------------------|-----------------------|------|-------------------------|
|              |                                                                                                                                                    | Min.                  | Typ. | Max.                    |
| $g_{fs}$     | $V_{DS} = 10\text{V}$ , $I_D = 0.5 \cdot I_{D25}$ , Note 1                                                                                         | 15                    | 27   | S                       |
| $C_{iss}$    | $V_{GS} = 0\text{V}$ , $V_{DS} = 25\text{V}$ , $f = 1\text{MHz}$                                                                                   |                       | 8700 | pF                      |
| $C_{oss}$    |                                                                                                                                                    |                       | 785  | pF                      |
| $C_{rss}$    |                                                                                                                                                    |                       | 315  | pF                      |
| $t_{d(on)}$  | <b>Resistive Switching Times</b><br>$V_{GS} = 10\text{V}$ , $V_{DS} = 0.5 \cdot V_{DSS}$ , $I_D = 0.5 \cdot I_{D25}$<br>$R_G = 1\Omega$ (External) |                       | 35   | ns                      |
| $t_r$        |                                                                                                                                                    |                       | 35   | ns                      |
| $t_{d(off)}$ |                                                                                                                                                    |                       | 75   | ns                      |
| $t_f$        |                                                                                                                                                    |                       | 21   | ns                      |
| $Q_{g(on)}$  | $V_{GS} = 10\text{V}$ , $V_{DS} = 0.5 \cdot V_{DSS}$ , $I_D = 0.5 \cdot I_{D25}$                                                                   |                       | 267  | nC                      |
| $Q_{gs}$     |                                                                                                                                                    |                       | 52   | nC                      |
| $Q_{gd}$     |                                                                                                                                                    |                       | 142  | nC                      |
| $R_{thJC}$   |                                                                                                                                                    |                       |      | 0.22 $^\circ\text{C/W}$ |
| $R_{thCS}$   |                                                                                                                                                    | 0.15                  |      | $^\circ\text{C/W}$      |

## Source-Drain Diode

| Symbol   | Test Conditions<br>( $T_J = 25^\circ\text{C}$ , unless otherwise specified)                           | Characteristic Values |      |               |
|----------|-------------------------------------------------------------------------------------------------------|-----------------------|------|---------------|
|          |                                                                                                       | Min.                  | Typ. | Max.          |
| $I_S$    | $V_{GS} = 0\text{V}$                                                                                  |                       |      | 24 A          |
| $I_{SM}$ | Repetitive, pulse width limited by $T_{JM}$                                                           |                       |      | 96 A          |
| $V_{SD}$ | $I_F = 24\text{A}$ , $V_{GS} = 0\text{V}$ , Note 1                                                    |                       |      | 1.5 V         |
| $t_{rr}$ | $I_F = 24\text{A}$ , $-di/dt = 100\text{A}/\mu\text{s}$<br>$V_R = 100\text{V}$ , $V_{GS} = 0\text{V}$ |                       |      | 250 ns        |
| $Q_{RM}$ |                                                                                                       | 1.0                   |      | $\mu\text{C}$ |
| $I_{RM}$ |                                                                                                       | 8.0                   |      | A             |

Note 1: Pulse test,  $t \leq 300\mu\text{s}$ ; duty cycle,  $d \leq 2\%$ .

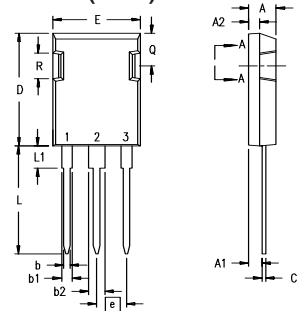
## TO-264 (IXFK) Outline



1 - GATE  
2, 4 - DRAIN (COLLECTOR)  
3 - SOURCE (EMITTER)

| SYM | INCHES   |       | MILLIMETERS |       |
|-----|----------|-------|-------------|-------|
|     | MIN      | MAX   | MIN         | MAX   |
| A   | .185     | .209  | 4.70        | 5.31  |
| A1  | .102     | .118  | 2.59        | 3.00  |
| b   | .037     | .055  | 0.94        | 1.40  |
| b1  | .087     | .102  | 2.21        | 2.59  |
| b2  | .110     | .126  | 2.79        | 3.20  |
| c   | .017     | .029  | 0.43        | 0.74  |
| D   | 1.007    | 1.047 | 25.58       | 26.59 |
| E   | .760     | .799  | 19.30       | 20.29 |
| e   | .215 BSC |       | 5.46 BSC    |       |
| J   | .000     | .010  | 0.00        | 0.25  |
| K   | .000     | .010  | 0.00        | 0.25  |
| L   | .779     | .842  | 19.79       | 21.39 |
| L1  | .087     | .102  | 2.21        | 2.59  |
| ØP  | .122     | .138  | 3.10        | 3.51  |
| Q   | .240     | .256  | 6.10        | 6.50  |
| Q1  | .330     | .346  | 8.38        | 8.79  |
| ØR  | .155     | .187  | 3.94        | 4.75  |
| ØR1 | .085     | .093  | 2.16        | 2.36  |
| S   | .243     | .253  | 6.17        | 6.43  |

## PLUS 247™ (IXFX) Outline



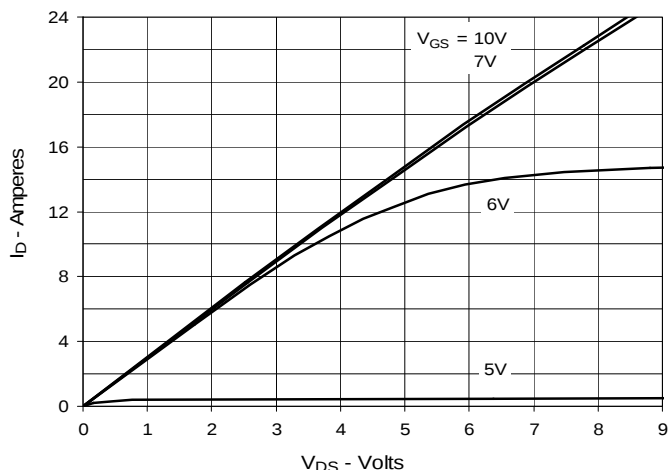
Terminals: 1 - Gate  
2 - Drain (Collector)  
3 - Source (Emitter)  
4 - Drain (Collector)

| Dim. | Millimeter |       | Inches   |       |
|------|------------|-------|----------|-------|
|      | Min.       | Max.  | Min.     | Max.  |
| A    | 4.83       | 5.21  | .190     | .205  |
| A1   | 2.29       | 2.54  | .090     | .100  |
| A2   | 1.91       | 2.16  | .075     | .085  |
| b    | 1.14       | 1.40  | .045     | .055  |
| b1   | 1.91       | 2.13  | .075     | .084  |
| b2   | 2.92       | 3.12  | .115     | .123  |
| C    | 0.61       | 0.80  | .024     | .031  |
| D    | 20.80      | 21.34 | .819     | .840  |
| E    | 15.75      | 16.13 | .620     | .635  |
| e    | 5.45 BSC   |       | .215 BSC |       |
| L    | 19.81      | 20.32 | .780     | .800  |
| L1   | 3.81       | 4.32  | .150     | .170  |
| Q    | 5.59       | 6.20  | .220     | 0.244 |
| R    | 4.32       | 4.83  | .170     | .190  |

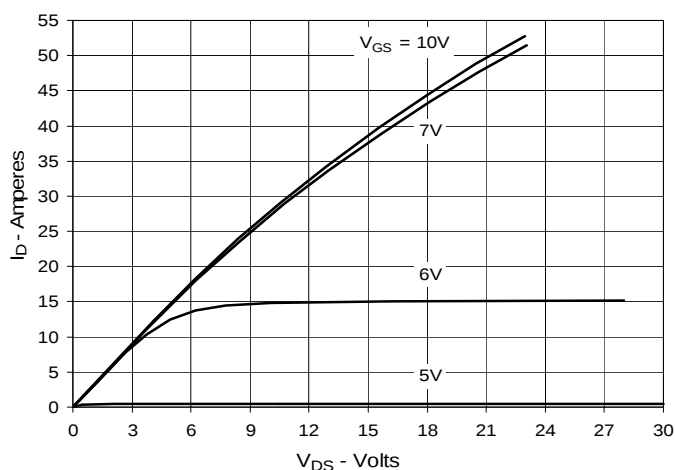
IXYS reserves the right to change limits, test conditions, and dimensions.

|                                                                                  |           |           |           |           |              |              |              |              |              |              |
|----------------------------------------------------------------------------------|-----------|-----------|-----------|-----------|--------------|--------------|--------------|--------------|--------------|--------------|
| IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: | 4,835,592 | 4,931,844 | 5,049,961 | 5,237,481 | 6,162,665    | 6,404,065 B1 | 6,683,344    | 6,727,585    | 7,005,734 B2 | 7,157,338 B2 |
|                                                                                  | 4,850,072 | 5,017,508 | 5,063,307 | 5,381,025 | 6,259,123 B1 | 6,534,343    | 6,710,405 B2 | 6,759,692    | 7,063,975 B2 |              |
|                                                                                  | 4,881,106 | 5,034,796 | 5,187,117 | 5,486,715 | 6,306,728 B1 | 6,583,505    | 6,710,463    | 6,771,478 B2 | 7,071,537    |              |

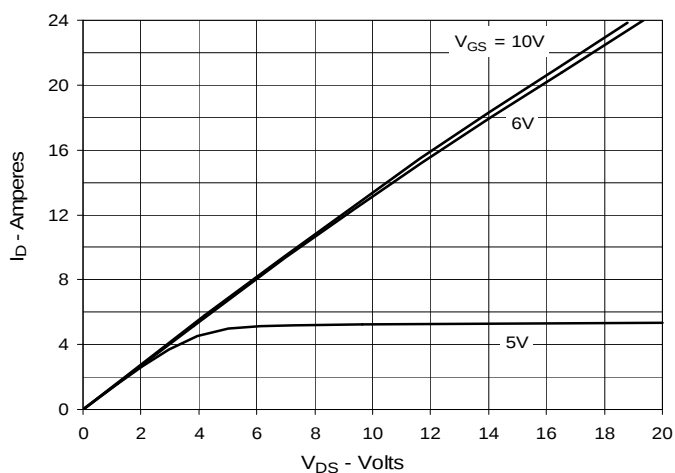
**Fig. 1. Output Characteristics  
@ 25°C**



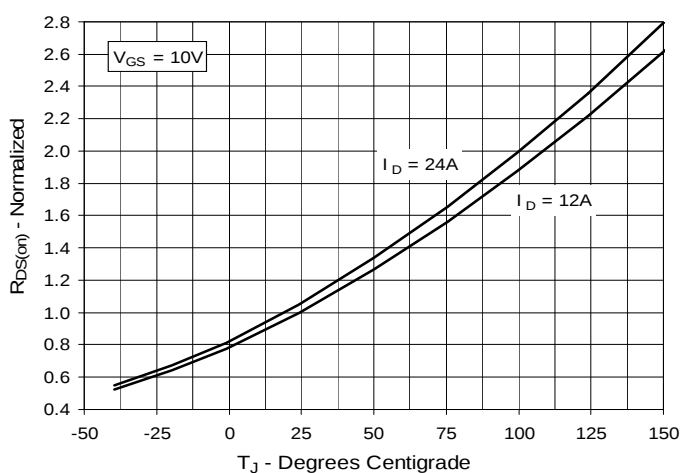
**Fig. 2. Extended Output Characteristics  
@ 25°C**



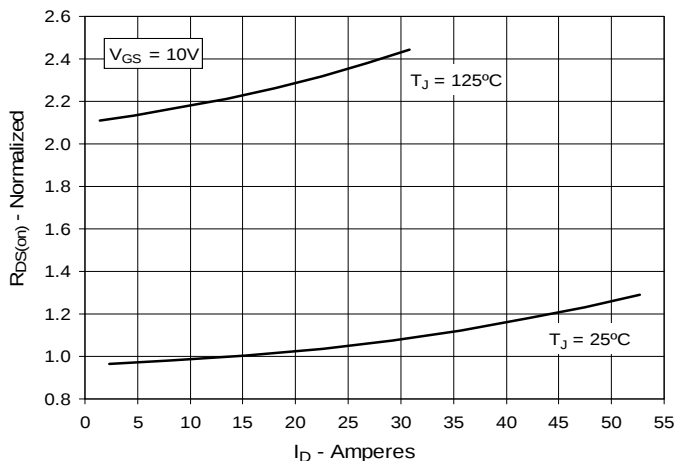
**Fig. 3. Output Characteristics  
@ 125°C**



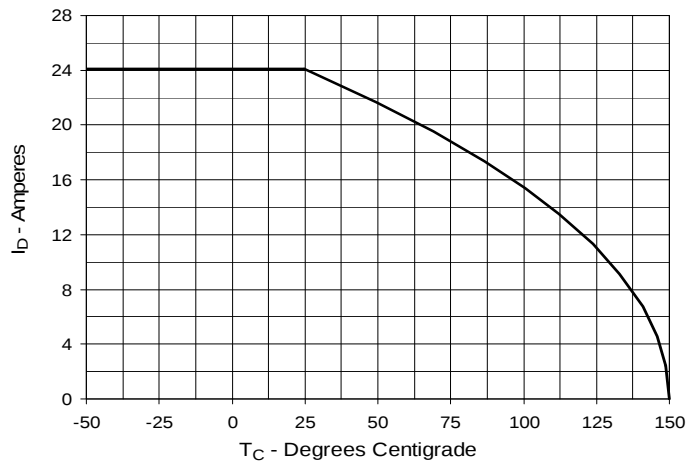
**Fig. 4.  $R_{DS(on)}$  Normalized to  $I_D = 12A$  Value  
vs. Junction Temperature**



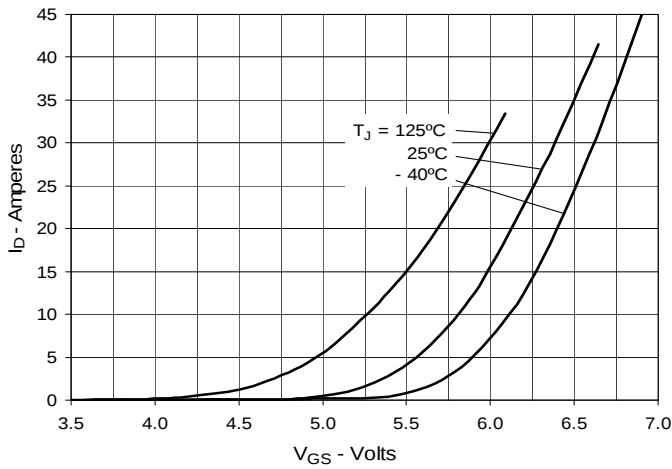
**Fig. 5.  $R_{DS(on)}$  Normalized to  $I_D = 12A$  Value  
vs. Drain Current**



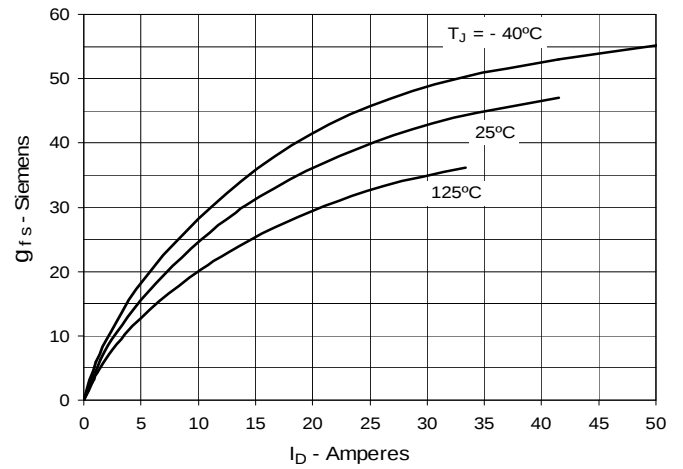
**Fig. 6. Maximum Drain Current vs.  
Case Temperature**



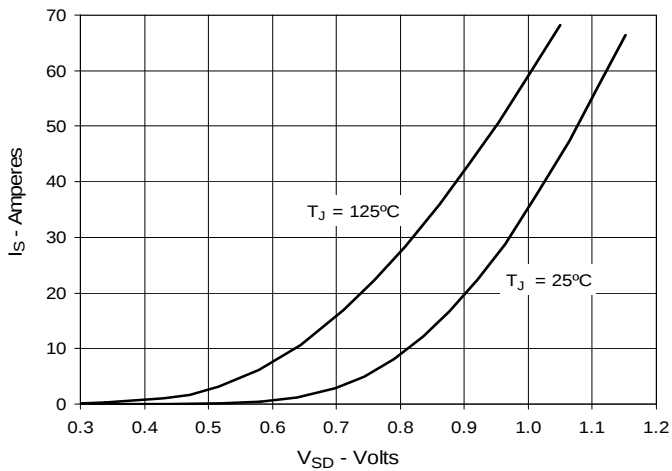
**Fig. 7. Input Admittance**



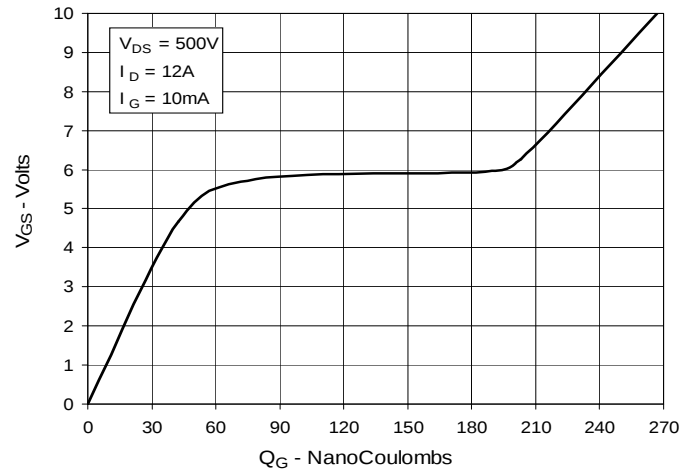
**Fig. 8. Transconductance**



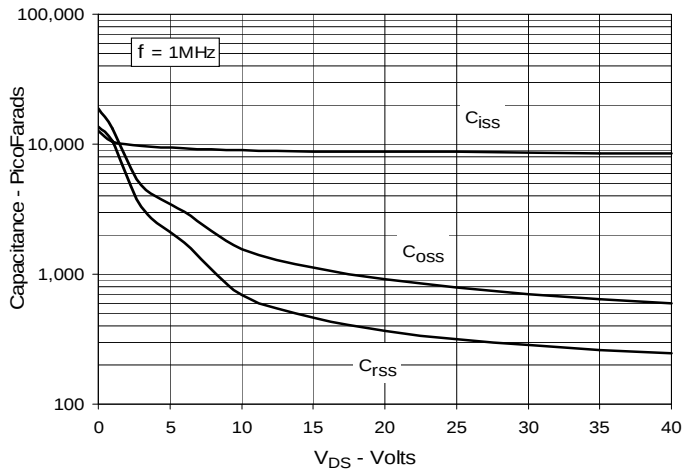
**Fig. 9. Forward Voltage Drop of Intrinsic Diode**



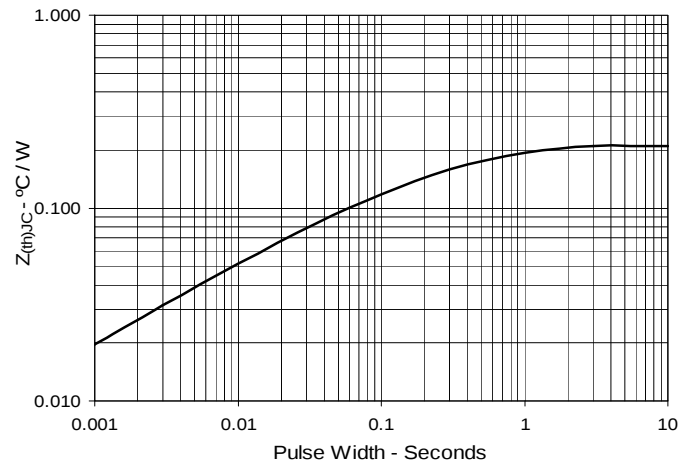
**Fig. 10. Gate Charge**



**Fig. 11. Capacitance**



**Fig. 12. Maximum Transient Thermal Impedance**





---

Disclaimer Notice - Information furnished is believed to be accurate and reliable. However, users should independently evaluate the suitability of and test each product selected for their own applications. Littelfuse products are not designed for, and may not be used in, all applications. Read complete Disclaimer Notice at [www.littelfuse.com/disclaimer-electronics](http://www.littelfuse.com/disclaimer-electronics).